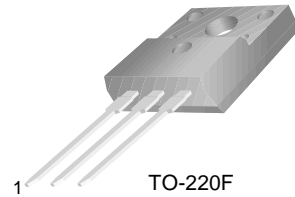


KSC5042F

High Voltage Switching Dynamic Focus Application

- High Collector-Emitter Breakdown Voltage : $BV_{CEO}=900V$
- Small $C_{ob}=2.8pF$ (Typ.)
- Wide S.O.A
- High reliability



TO-220F
1.Base 2.Collector 3.Emitter

NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ C$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------|--|------------|------------|
| V_{CBO} | Collector-Base Voltage | 1500 | V |
| V_{CEO} | Collector-Emitter Voltage | 900 | V |
| V_{EBO} | Emitter-Base Voltage | 5 | V |
| I_C | Collector Current (DC) | 100 | mA |
| I_{CP} | Collector Current (Pulse) | 300 | mA |
| P_C | Collector Dissipation ($T_C=25^\circ C$) | 6 | W |
| T_J | Junction Temperature | 150 | $^\circ C$ |
| T_{STG} | Storage Temperature | - 55 ~ 150 | $^\circ C$ |

Electrical Characteristics $T_C=25^\circ C$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|---------------|--------------------------------------|---------------------------|------|------|------|---------|
| BV_{CBO} | Collector-Base Breakdown Voltage | $I_C = 1mA, I_E = 0$ | 1500 | | | V |
| BV_{CEO} | Collector-Emitter Breakdown Voltage | $I_C = 5mA, I_B = 0$ | 900 | | | V |
| BV_{EBO} | Emitter-Base Breakdown Voltage | $I_E = 1mA, I_C = 0$ | 5 | | | V |
| I_{CBO} | Collector Cut-off Current | $V_{CB} = 900V, I_E = 0$ | | | 10 | μA |
| I_{EBO} | Emitter Cut-off Current | $V_{EB} = 4V, I_C = 0$ | | | 10 | μA |
| h_{FE} | DC Current Gain | $V_{CE} = 5V, I_C = 10mA$ | 30 | | | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 20mA, I_B = 4mA$ | | | 5 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C = 20mA, I_B = 4mA$ | | | 2 | V |
| C_{ob} | Output Capacitance | $V_{CB} = 100V, f = 1MHz$ | | 2.8 | | pF |

Typical Characteristics

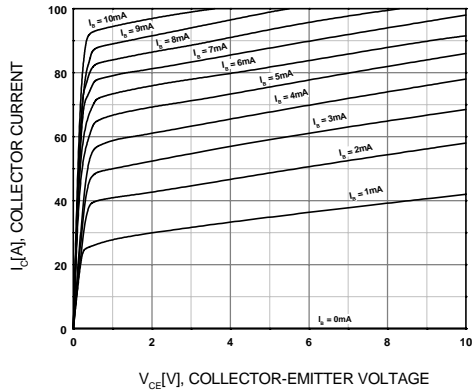


Figure 1. Static Characteristic

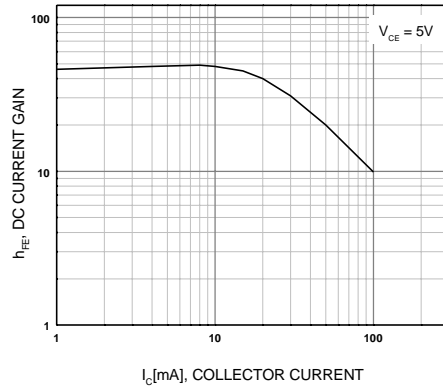


Figure 2. DC current Gain

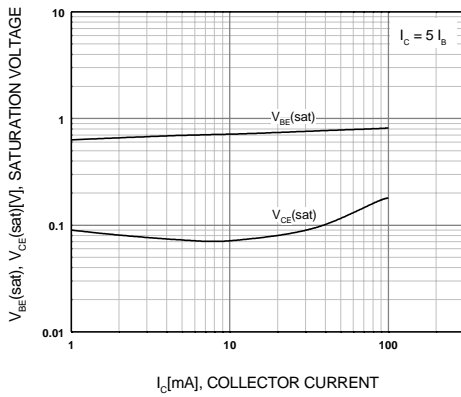


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

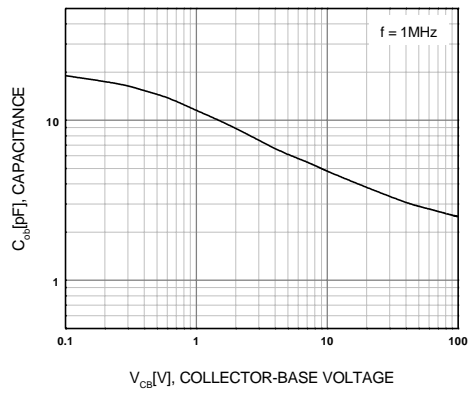


Figure 4. Collector-Base Capacitance

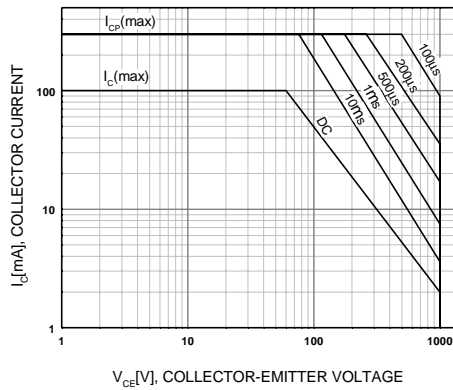


Figure 5. Safe Operating Area

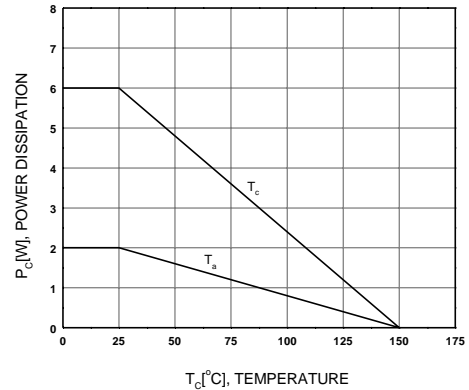
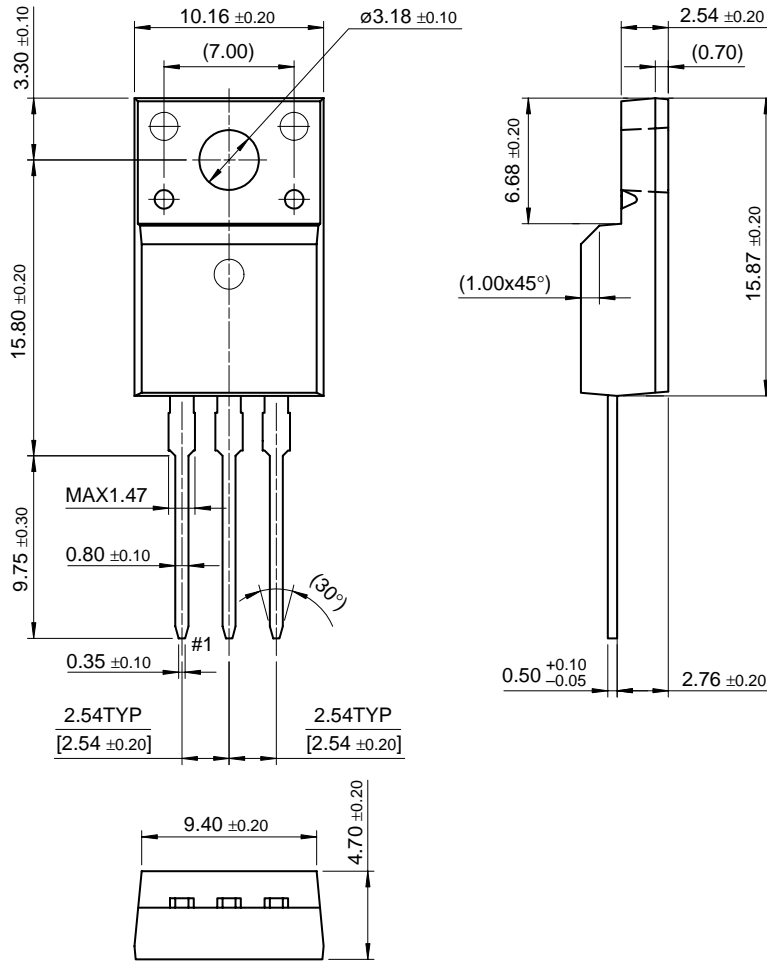


Figure 6. Power Derating

Package Dimensions

KSC5042F

TO-220F



Dimensions in Millimeters

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